

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE  
WASHINGTON, D.C. 20231**

Appl No.: **10/758,132**  
Applicant: **Jeng et al.**  
Filing Date: **1/16/2004**  
Art Unit: **2812**  
Examiner: **Richard Booth**  
Attorney Docket No.: **18806.024**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**INTERVIEW SUMMARY AND AMENDMENT**

Dear Sir:

The applicant hereby thank the examiners for the personl interview conducted on March 6, 2007. The applicant hereby files written statement of the reasons presented at the March 6, 2007 personal interview as warranting favorable action.

Halliyal reference was discussed in detail, and Primary Examiner Richard Booth made the determination that the claims as proposed read over the Halliyal reference, as Halliyal reference does not disclose implanting hetero element on the top layer of the gate dielectric layers so as to provide an increased electron trapping density in the gate dielectric layers.

**Claims** presented are reflected in the listing of claims which begins on page 2 of this paper.

**Specification** are amended to correct grammatical errors on page 4 of this paper.